

OSRAM LE B Q7WN

Datasheet

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Tobelbader Strasse 30, 8141 Premstaetten, Austria

Phone +43 3136 500-0

ams-osram.com

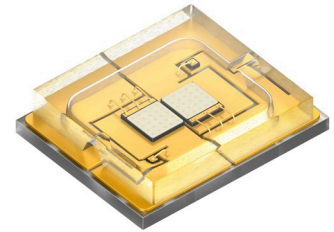
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OSRAM OSTAR™ Projection Compact

LE B Q7WN

The OSTAR Projection LE B Q7WN is specifically designed for automotive head-up applications using a DMD.



Applications

- Projection
- Projection & Display
- Visualization

Features

- Package: compact lightsource in SMT technology with glass window on top
- Chip technology: UX:3
- Typ. Radiation: 120° (Lambertian emitter)
- Color: $\lambda_{\text{dom}} = 455 \text{ nm}$ (• blue)
- Corrosion Robustness Class: 3B
- Qualifications: AEC-Q102 Qualified
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)

Ordering Information

Type	Total radiant flux ¹⁾ $I_F = 1000 \text{ mA}$ Φ_e	Ordering Code
LE B Q7WN-7B7C-25	2240 ... 4000 mW	Q65113A8298

Maximum Ratings

Parameter	Symbol		Values
Operating Temperature	T_{op}	min.	-40 °C
		max.	125 °C
Storage Temperature	T_{stg}	min.	-40 °C
		max.	125 °C
Junction Temperature	T_j	max.	150 °C
Forward Current $T_s = 25\text{ °C}$; per chip	I_F	min.	40 mA
		max.	3000 mA
Forward Current pulsed $T_s = 25\text{ °C}$; per chip	$I_{F\ pulse}$		4000 mA
ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)	V_{ESD}		2 kV
Reverse current ²⁾	I_R	max.	200 mA

Characteristics

$I_F = 1000 \text{ mA}$; $T_S = 25 \text{ °C}$; per chip

Parameter	Symbol		Values
Peak Wavelength	λ_{peak}	typ.	450 nm
Dominant Wavelength ³⁾	λ_{dom}	min.	445 nm
		typ.	455 nm
		max.	461 nm
Spectral bandwidth at 50% $I_{\text{rel,max}}$	$\Delta\lambda$	typ.	17 nm
Viewing angle at 50% I_V	2ϕ	typ.	120 °
Radiating surface	A_{color}	typ.	ca. 0.96 x 2.03 mm ²
Partial Flux acc. CIE 127:2007 ⁴⁾ $I_F = 1000 \text{ mA}$	$\Phi_{E/V, 120^\circ}$	typ.	0.77
Forward Voltage ⁵⁾ $I_F = 1000 \text{ mA}$	V_F	min.	2.75 V
		typ.	3.00 V
		max.	3.50 V
Reverse voltage (ESD device)	$V_{R \text{ ESD}}$	min.	45 V
Reverse voltage ²⁾ $I_R = 20 \text{ mA}$	V_R	max.	1.2 V
Real thermal resistance junction/solderpoint ⁶⁾	$R_{\text{thJS real}}$	typ.	1.7 K / W
		max.	2.1 K / W
Electrical thermal resistance junction/solderpoint ⁶⁾ with efficiency $\eta_e = 20 \%$	$R_{\text{thJS elec.}}$	typ.	1.4 K / W
		max.	1.7 K / W

Brightness Groups

Group	Total radiant flux ¹⁾ $I_F = 1000 \text{ mA}$ min. Φ_e	Total radiant flux ¹⁾ $I_F = 1000 \text{ mA}$ max. Φ_e
7B	2240 mW	2500 mW
8B	2500 mW	2800 mW
5C	2800 mW	3150 mW
6C	3150 mW	3550 mW
7C	3550 mW	4000 mW

Forward Voltage Groups

Group	Forward Voltage ⁵⁾ $I_F = 1000 \text{ mA}$ min. V_F	Forward Voltage ⁵⁾ $I_F = 1000 \text{ mA}$ max. V_F
0	2.75 V	3.50 V

Wavelength Groups

Group	Dominant Wavelength ³⁾ min. λ_{dom}	Dominant Wavelength ³⁾ max. λ_{dom}
2	445 nm	449 nm
3	449 nm	453 nm
4	453 nm	457 nm
5	457 nm	461 nm

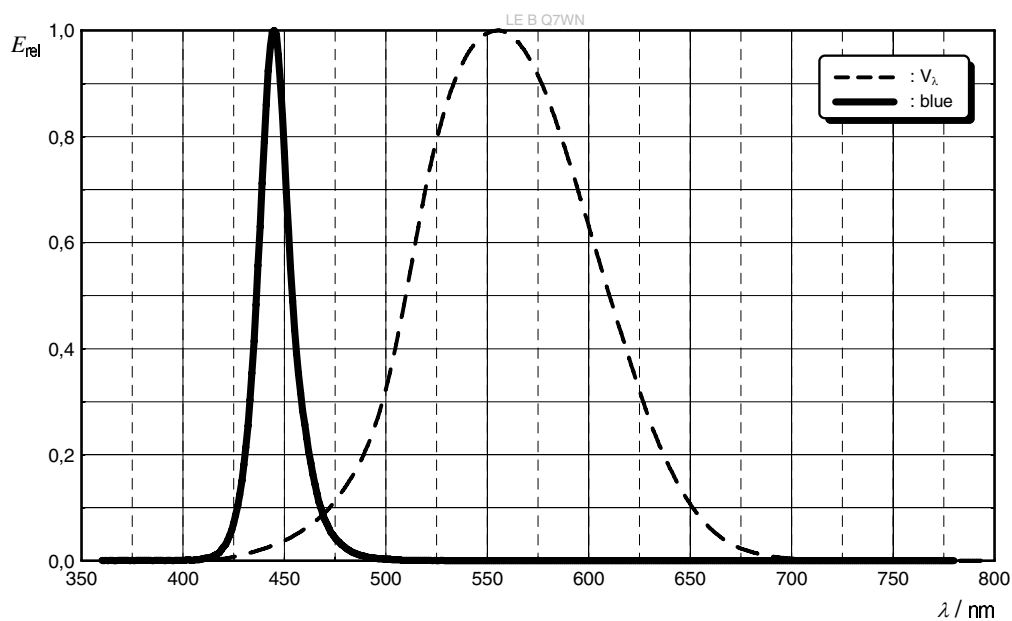
Group Name on Label

Example: 5C-2

Brightness	Wavelength
5C	2

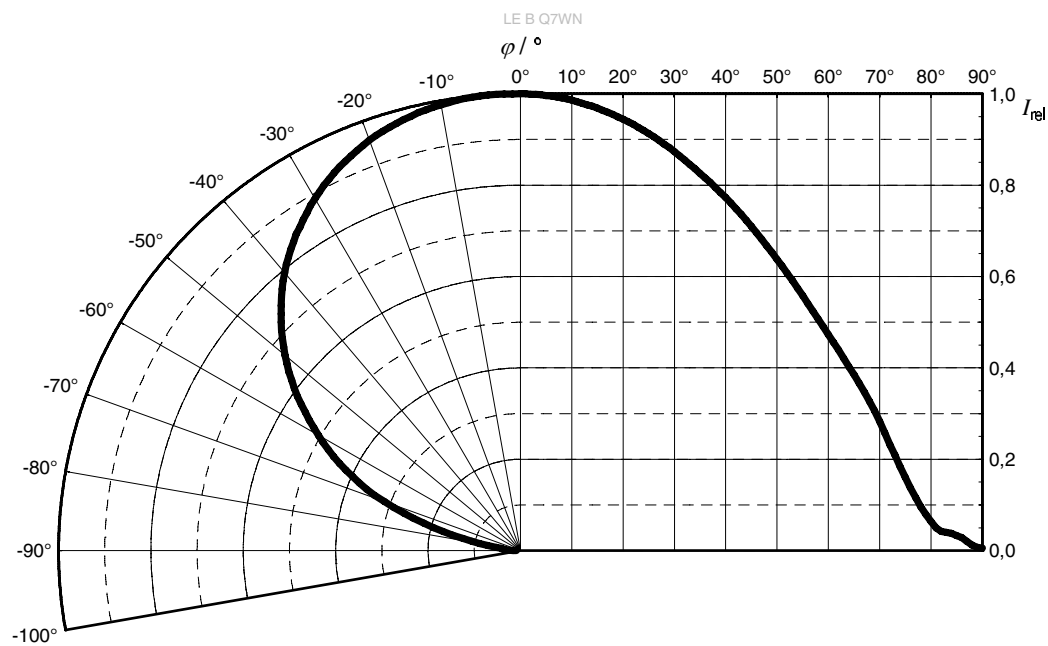
Relative Spectral Emission ⁴⁾

$E_{\text{rel}} = f(\lambda)$; $I_F = 1000 \text{ mA}$; $T_J = 25^\circ\text{C}$; per Chip



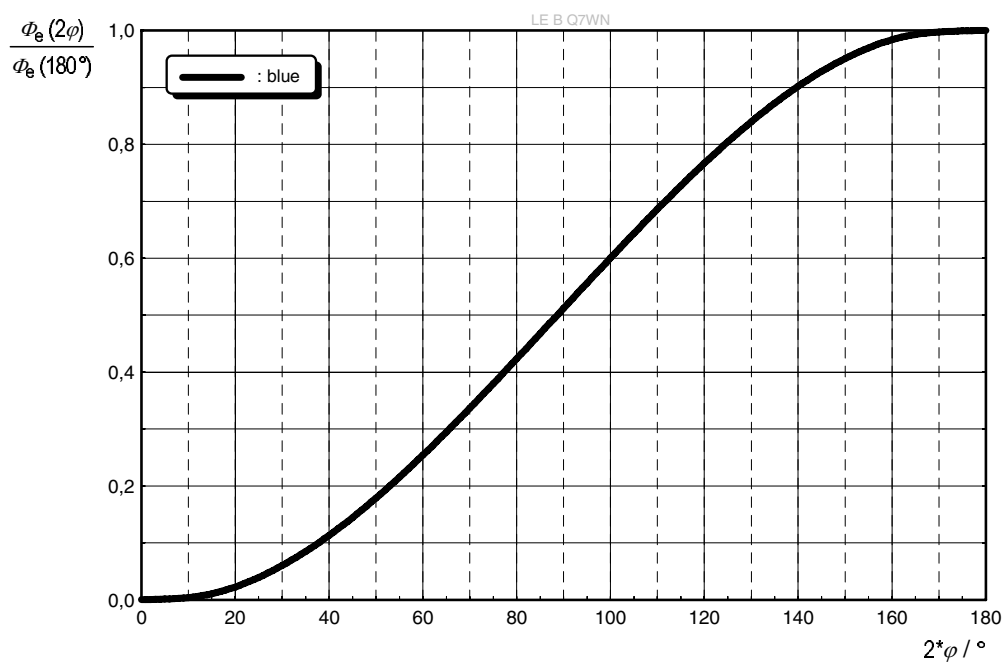
Radiation Characteristics ⁴⁾

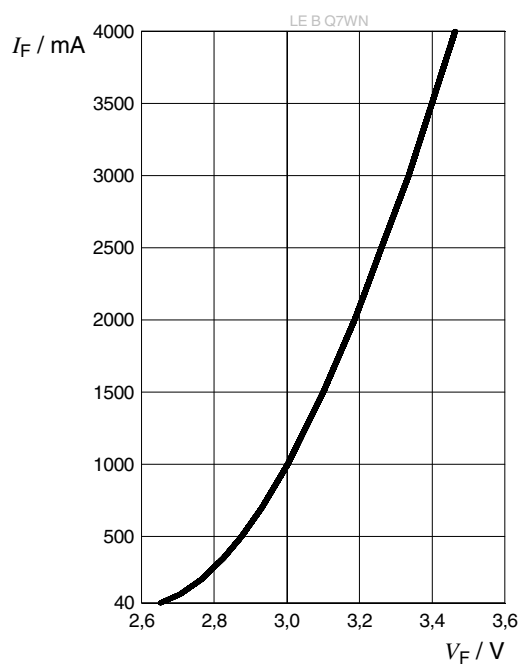
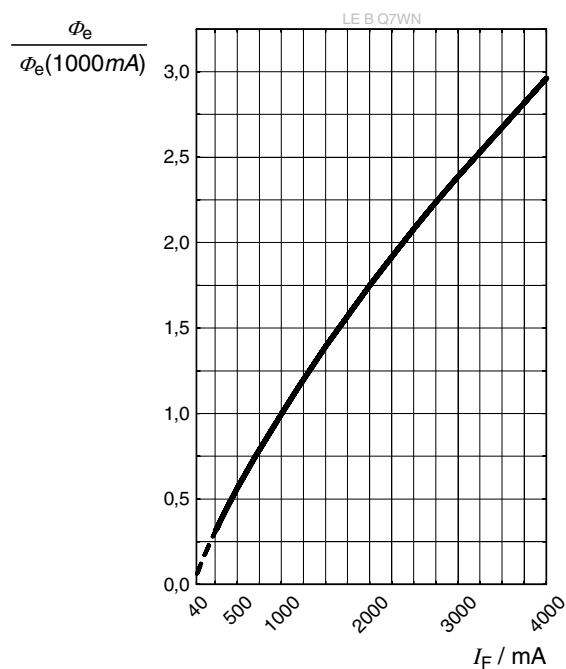
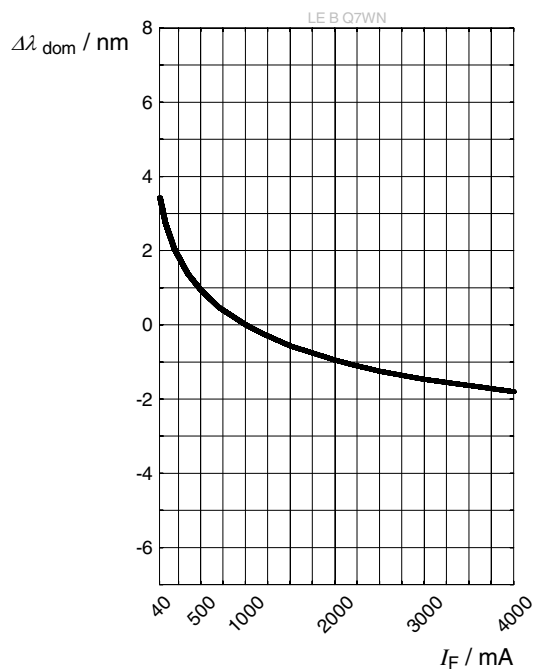
$I_{\text{rel}} = f(\varphi)$; $T_J = 25^\circ\text{C}$

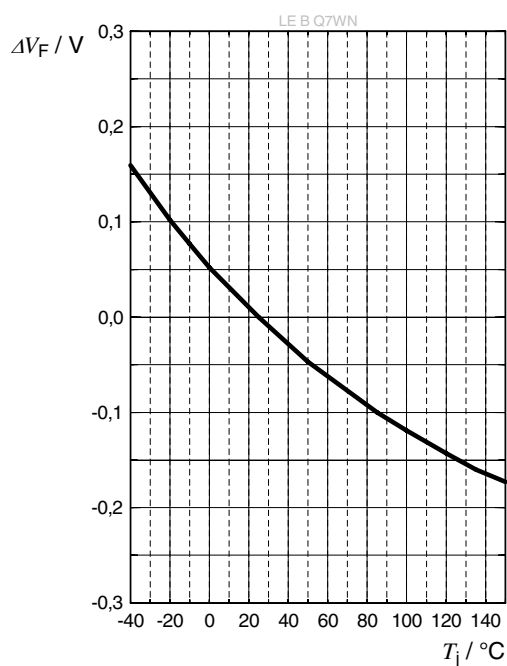
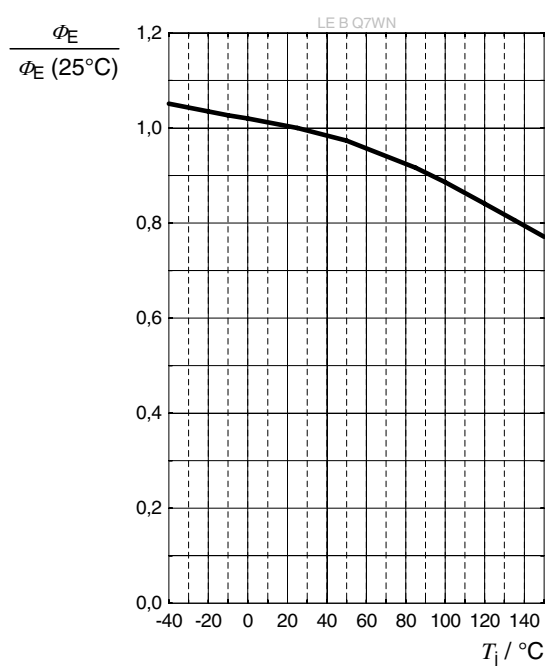
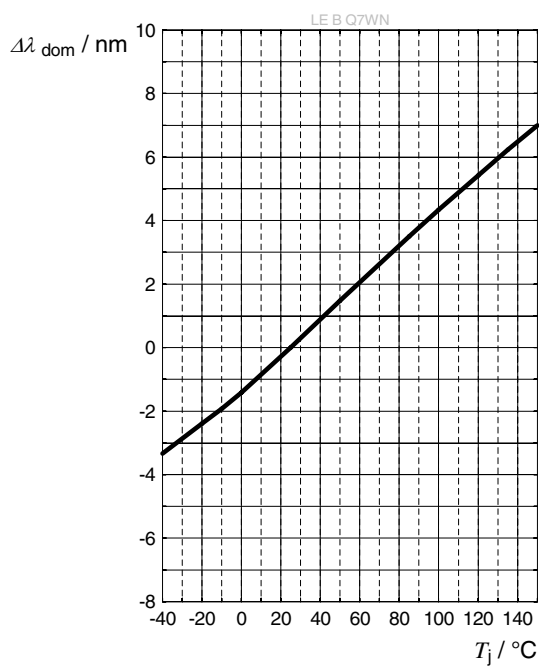


Relative Partial Flux ⁴⁾

$$\Phi_E(2\varphi)/\Phi_E(180^\circ) = f(\varphi); T_J = 25^\circ\text{C}$$

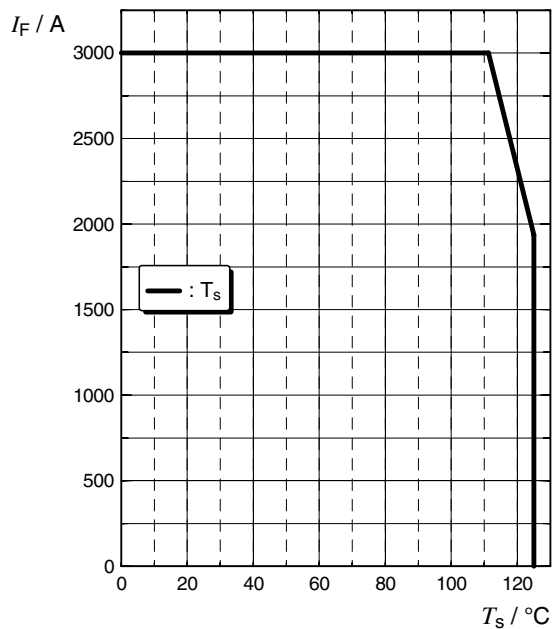


Forward current ⁴⁾ $I_F = f(V_F); T_J = 25\text{ °C}; \text{ per Chip}$ **Relative Radiant Power** ^{4), 7)} $\Phi_E / \Phi_E(1000\text{ mA}) = f(I_F); T_J = 25\text{ °C}; \text{ per Chip}$ **Dominant Wavelength** ⁴⁾ $\Delta\lambda_{\text{dom}} = f(I_F); T_J = 25\text{ °C}; \text{ per Chip}$ 

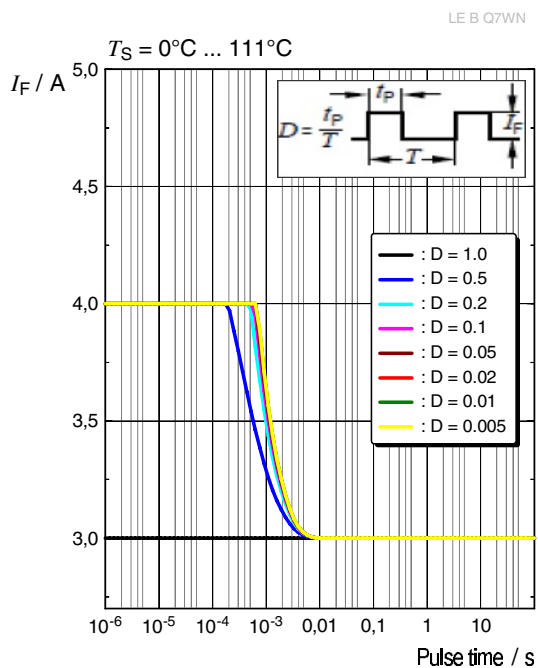
Forward Voltage ⁴⁾ $\Delta V_F = V_F - V_F(25\text{ °C}) = f(T_j); I_F = 1000\text{ mA}; \text{ per Chip}$ **Relative Radiant Power** ⁴⁾ $\Phi_E / \Phi_E(25\text{ °C}) = f(T_j); I_F = 1000\text{ mA}; \text{ per Chip}$ **Dominant Wavelength** ⁴⁾ $\Delta \lambda_{\text{dom}} = \lambda_{\text{dom}} - \lambda_{\text{dom}}(25\text{ °C}) = f(T_j); I_F = 1000\text{ mA}; \text{ per Chip}$ 

Max. Permissible Forward Current ⁶⁾

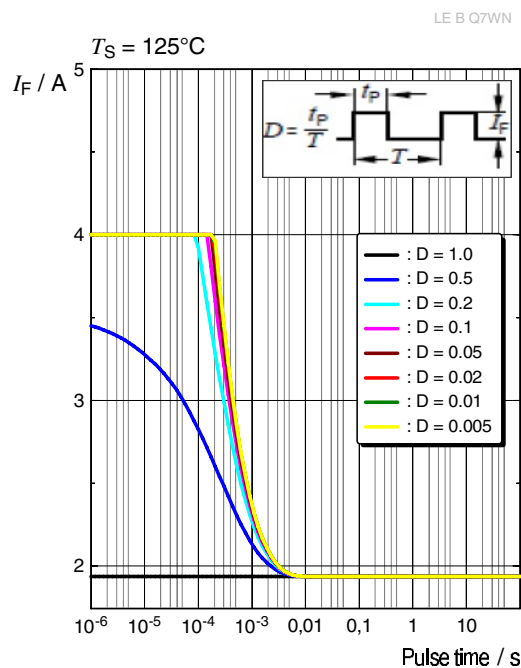
$$I_F = f(T)$$

**Permissible Pulse Handling Capability**

$$I_F = f(t_p); D: \text{Duty cycle}$$

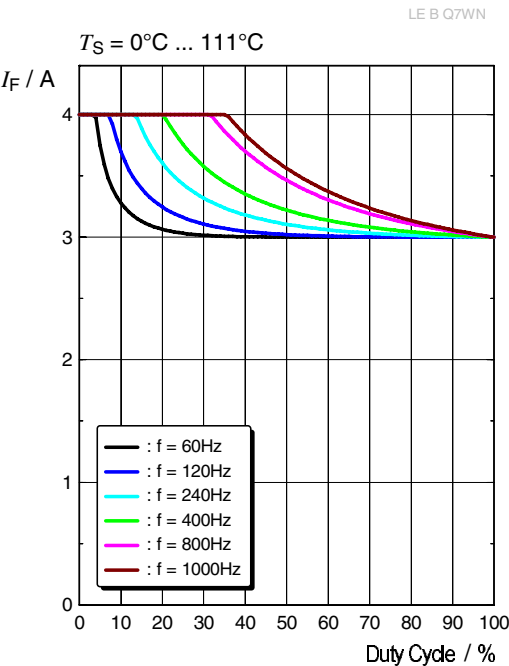
**Permissible Pulse Handling Capability**

$$I_F = f(t_p); D: \text{Duty cycle}$$



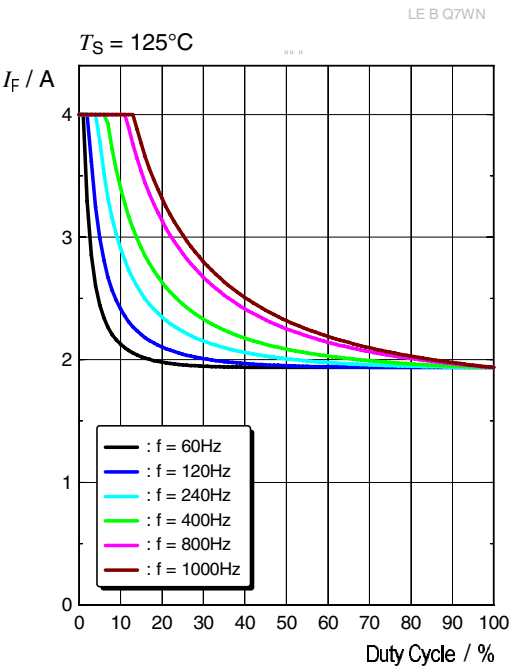
Permissible F. Handling Capability

f: Frequency

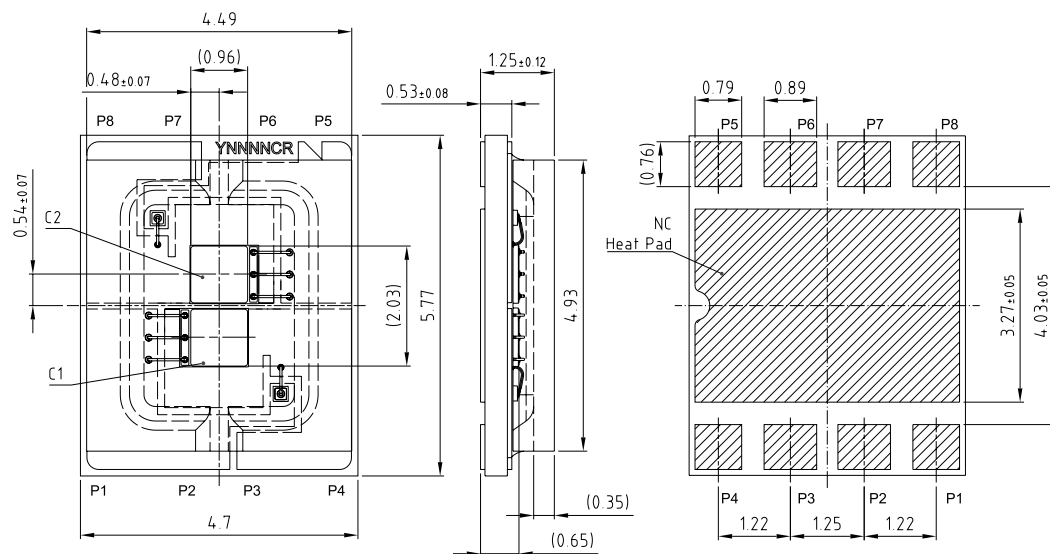


Permissible F. Handling Capability

f: Frequency



Dimensional Drawing ⁸⁾



general tolerance ± 0.1
lead finish Au 

Pinning:
P1, P2 Anode C1
P3, P4 Cathode C1
P5, P6 Anode C2
P7, P8 Cathode C2

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Further Information:

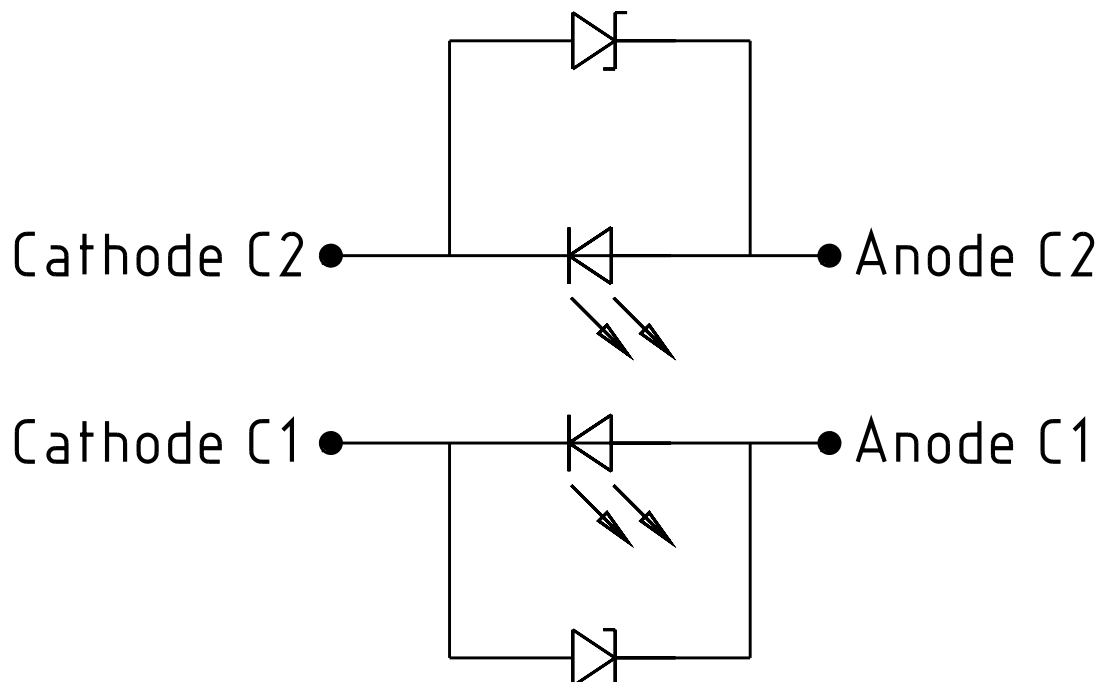
Approximate Weight: 85.0 mg

Package marking: Cathode

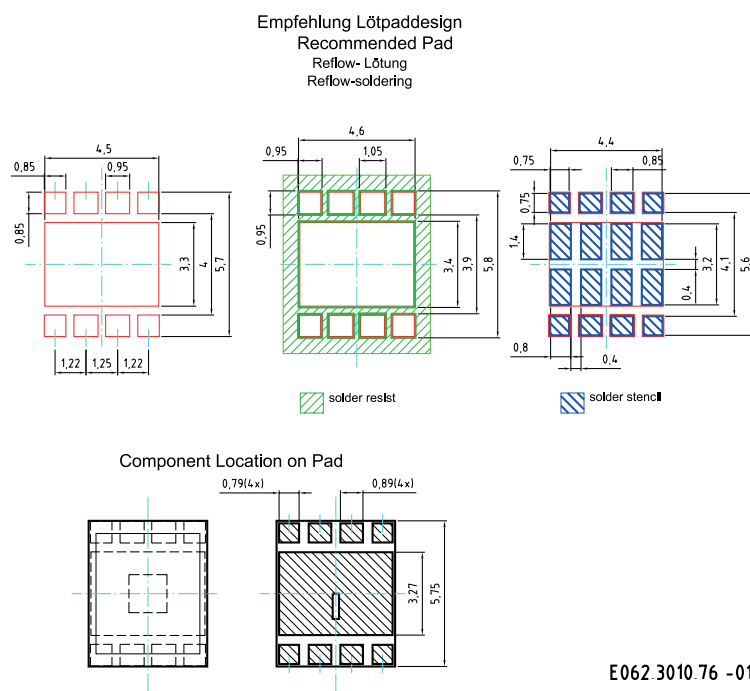
Corrosion test: Class: 3B
Test condition: 40°C / 90 % RH / 15 ppm H₂S / 14 days (stricter than IEC 60068-2-43)

ESD advice: The device is protected by ESD device which is connected in parallel to the Chip.

Electrical Internal Circuit



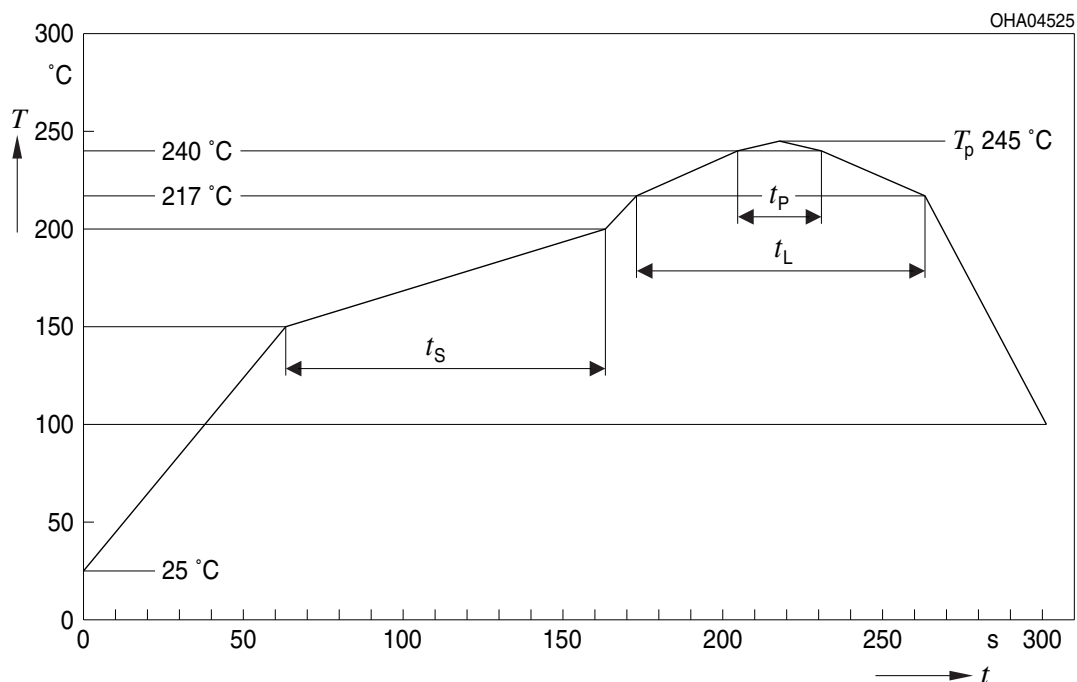
Recommended Solder Pad ⁸⁾



Do not use exposed copper MCPCB technology for automotive applications. For superior solder joint connectivity results we recommend soldering under standard nitrogen atmosphere. Package not suitable for any kind of wet cleaning or ultrasonic cleaning.

Reflow Soldering Profile

Product complies to MSL Level 2 acc. to JEDEC J-STD-020E

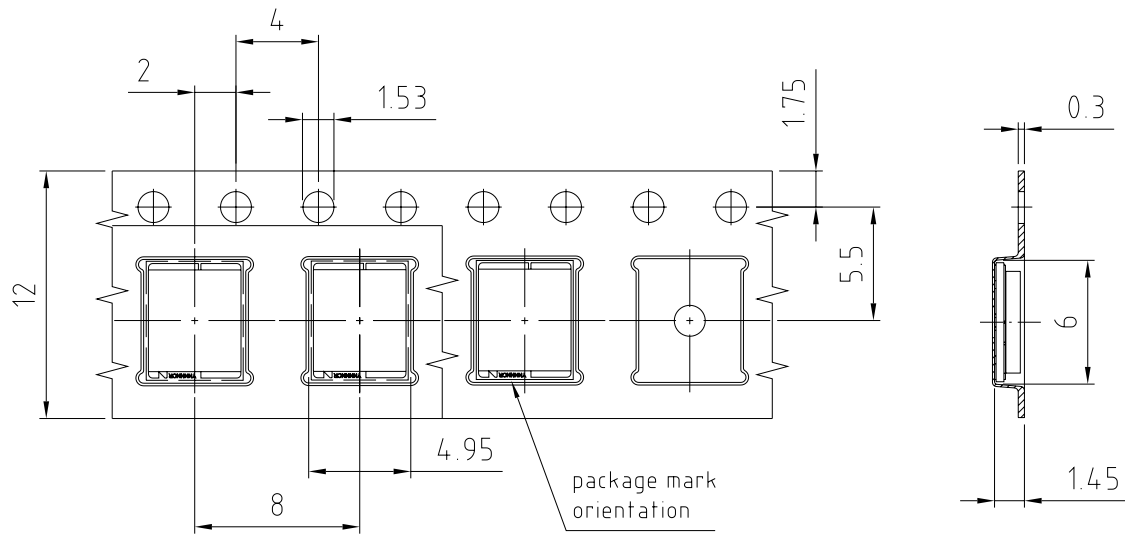


Profile Feature	Symbol	Pb-Free (SnAgCu) Assembly			Unit
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat ^{*)} 25°C to 150°C			2	3	K/s
Time t_s T_{Smin} to T_{Smax}	t_s	60	100	120	s
Ramp-up rate to peak ^{*)} T_{Smax} to T_p			2	3	K/s
Liquidus temperature	T_L		217		$^{\circ}\text{C}$
Time above liquidus temperature	t_L		80	100	s
Peak temperature	T_p		245	260	$^{\circ}\text{C}$
Time within 5°C of the specified peak temperature $T_p - 5\text{ K}$	t_p	10	20	30	s
Ramp-down rate [*] T_p to 100°C			3	6	K/s
Time 25°C to T_p				480	s

All temperatures refer to the center of the package, measured on the top of the component

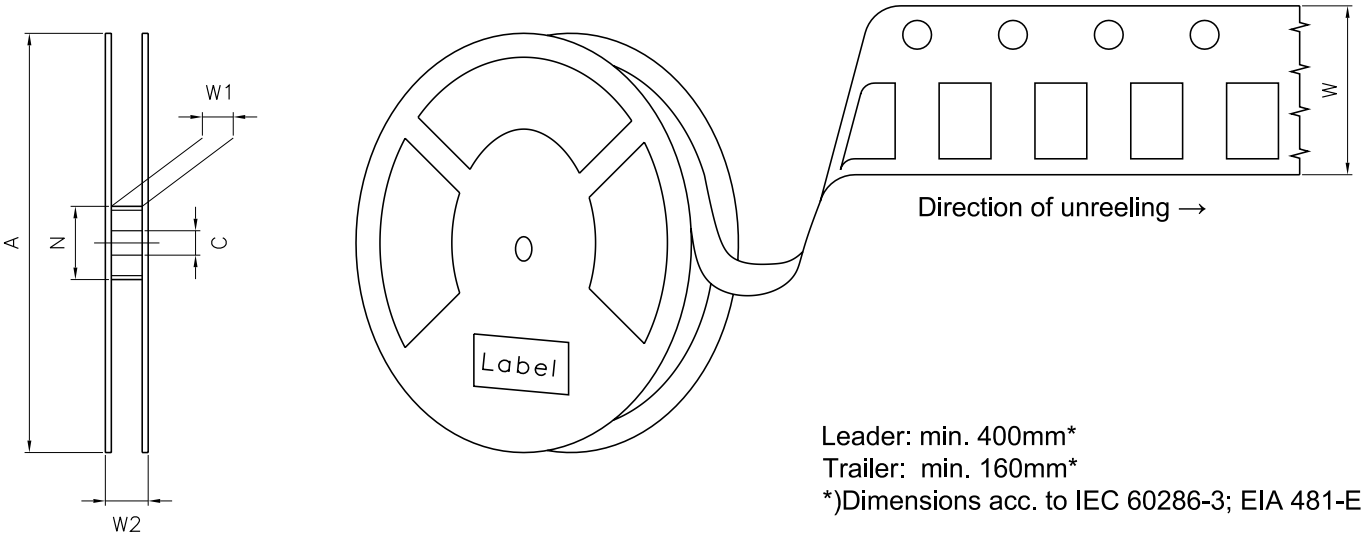
* slope calculation DT/Dt : Dt max. 5 s; fulfillment for the whole T-range

Taping ⁸⁾



C67062-A0481-B8-02

Tape and Reel ⁹⁾



Reel Dimensions

A	W	N _{min}	W ₁	W _{2max}	Pieces per PU
180 mm	12 + 0.3 / - 0.1 mm	60 mm	12.4 + 2 mm	18.4 mm	1000

Barcode-Product-Label (BPL)

OSRAM

LX XXXX

BIN1: XX-XX-X-XXX-X

(6P) BATCH NO: 1234567890

RoHS Compliant

(1T) LOT NO: 1234567890

(9D) D/C: 1234

ML Temp

ST

X

XXX °C X

Pack: RXX

DEMY XXX

X_X123_1234.1234 X

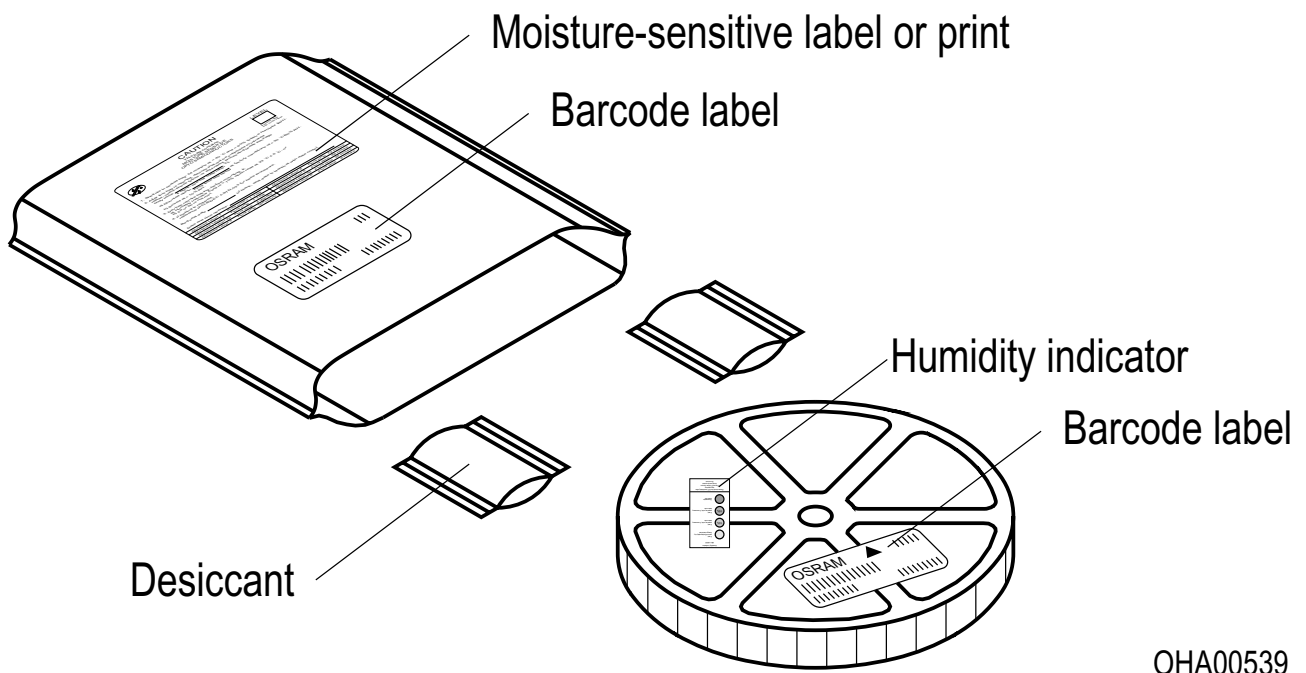
(X) PROD NO: 123456789

(Q) QTY: 9999

(G) GROUP: XX-XX-X-X

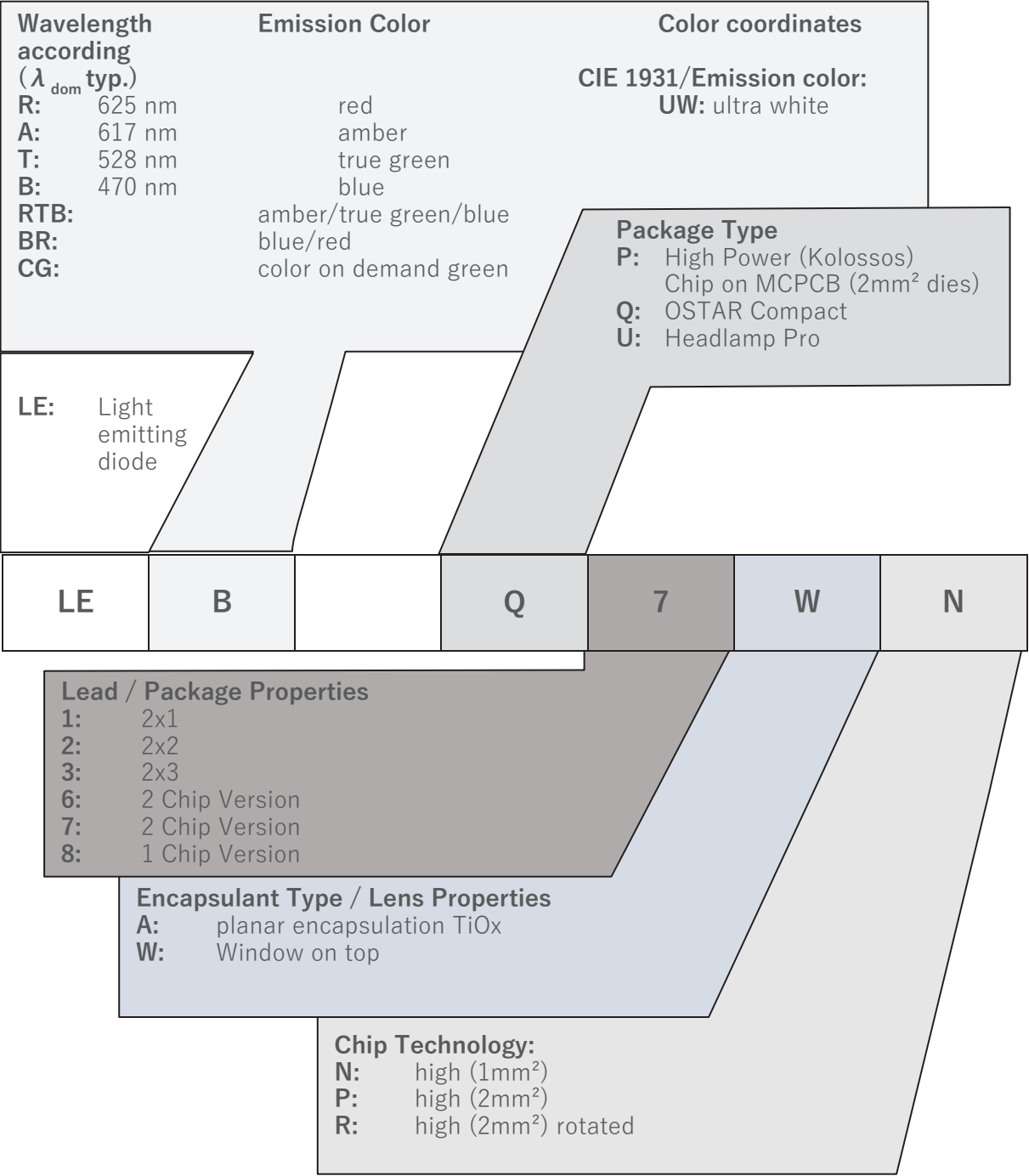
OHA04563

Dry Packing Process and Materials ⁸⁾



Moisture-sensitive product is packed in a dry bag containing desiccant and a humidity card according JEDEC-STD-033.

Type Designation System



Notes

The evaluation of eye safety occurs according to the standard IEC 62471:2006 (photo biological safety of lamps and lamp systems). Within the risk grouping system of this IEC standard, the device specified in this data sheet fall into the class **high risk (exposure time less than 0.25 s)**. Under real circumstances (for exposure time, conditions of the eye pupils, observation distance), it is assumed that no endangerment to the eye exists from these devices. As a matter of principle, however, it should be mentioned that intense light sources have a high secondary exposure potential due to their blinding effect. When looking at bright light sources (e.g. headlights), temporary reduction in visual acuity and afterimages can occur, leading to irritation, annoyance, visual impairment, and even accidents, depending on the situation.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit <https://ams-osram.com/support/application-notes>

Disclaimer

Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on our website.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Product and functional safety devices/applications or medical devices/applications

Our components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

Our products are not qualified at module and system level for such application.

In case buyer – or customer supplied by buyer – considers using our components in product safety devices/ applications or medical devices/applications, buyer and/or customer has to inform our local sales partner immediately and we and buyer and /or customer will analyze and coordinate the customer-specific request between us and buyer and/or customer.

Glossary

- 1) **Brightness:** Brightness values are measured during a current pulse of typically 25 ms, with an internal reproducibility of $\pm 8\%$ and an expanded uncertainty of $\pm 11\%$ (acc. to GUM with a coverage factor of $k = 3$).
- 2) **Reverse Operation:** This product is intended to be operated applying a forward current within the specified range. Applying any continuous reverse bias or forward bias below the voltage range of light emission shall be avoided because it may cause migration which can change the electro-optical characteristics or damage the LED.
- 3) **Wavelength:** The wavelength is measured at a current pulse of typically 25 ms, with an internal reproducibility of ± 0.5 nm and an expanded uncertainty of ± 1 nm (acc. to GUM with a coverage factor of $k = 3$).
- 4) **Typical Values:** Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 5) **Forward Voltage:** The forward voltage is measured during a current pulse of typically 8 ms, with an internal reproducibility of ± 0.05 V and an expanded uncertainty of ± 0.1 V (acc. to GUM with a coverage factor of $k = 3$).
- 6) **Thermal Resistance:** $R_{th\ max}$ is based on statistic values (6σ) used for Derating.
- 7) **Characteristic curve:** In the range where the line of the graph is broken, you must expect higher differences between single devices within one packing unit.
- 8) **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with ± 0.1 and dimensions are specified in mm.
- 9) **Tape and Reel:** All dimensions and tolerances are specified acc. IEC 60286-3 and specified in mm.

Revision History

Version	Date	Change
1.0	2025-06-25	Initial Version



EU RoHS and China RoHS compliant product

此产品符合欧盟 RoHS 指令的要求；
按照中国的相关法规和标准，
不含有毒有害物质或元素。

Published by ams-OSRAM AG

Tobelbader Strasse 30, 8141 Premstaetten, Austria

Phone +43 3136 500-0

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